# OC1005

## N-channel TrenchMOS standard level FET

**Rev. 02 — 10 December 2007** **Product data sheet**

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology.

### 1.2 Features

- Standard level threshold
- Very low on-state resistance

### 1.3 Applications

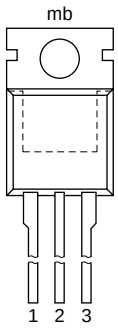
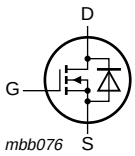
- Motors, lamps, solenoids
- DC-to-DC converters
- Uninterrupted power supplies
- General industrial applications.

### 1.4 Quick reference data

- $V_{DS} \leq 55$ V
- $I_D \leq 110$ A
- $P_{tot} \leq 200$ W
- $R_{DSon} \leq 7.1$ mΩ

## 2. Pinning information

**Table 1. Pinning**

| Pin | Description | Simplified outline | Symbol |
|---|---|---|---|
| 1 | gate (G) |   |   |
| 2 | drain (D) | | |
| 3 | source (S) | | |
| mb | mounting base; connected to drain | | |
| | | SOT78 (TO-220AB) | |

## 3. Ordering information

**Table 2. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| OC1005 | SC-46 | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

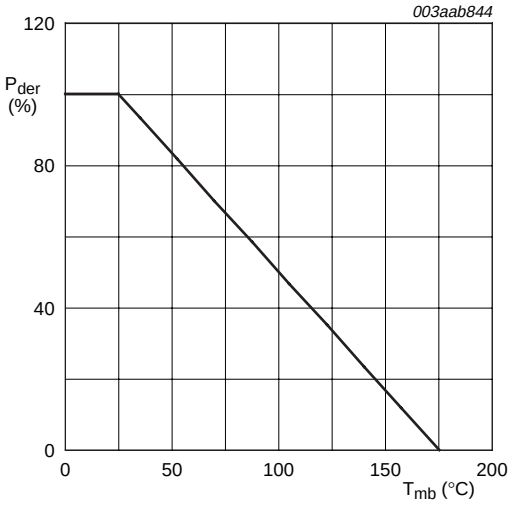
## 4. Limiting values

**Table 3. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

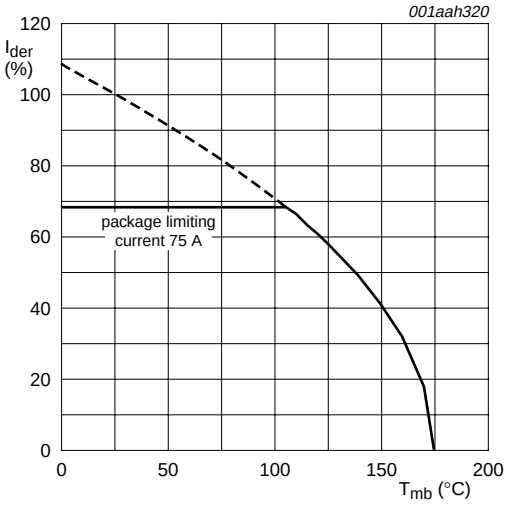
| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | 25 °C ≤ $T_j$ ≤ 175 °C | | - | 55 | V |
| $V_{DGR}$ | drain-gate voltage (DC) | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ | | - | 55 | V |
| $V_{GS}$ | gate-source voltage | | | - | ±20 | V |
| $I_D$ | drain current | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 2 and 3 | [1] | - | 110 | A |
| | | $T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see Figure 2 | | - | 80 | A |
| $I_{DM}$ | peak drain current | $T_{mb}$ = 25 °C; pulsed; $t_p$ ≤ 10 µs; see Figure 3 | | - | 390 | A |
| $P_{tot}$ | total power dissipation | $T_{mb}$ = 25 °C; see Figure 1 | | - | 200 | W |
| $T_{stg}$ | storage temperature | | | –55 | +175 | °C |
| $T_j$ | junction temperature | | | –55 | +175 | °C |
| **Source-drain diode** | | | | | | |
| $I_S$ | source current | $T_{mb}$ = 25 °C | [1] | - | 110 | A |
| $I_{SM}$ | peak source current | $T_{mb}$ = 25 °C; pulsed; $t_p$ ≤ 10 µs | | - | 390 | A |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | unclamped inductive load; $I_D$ = 75 A; $t_p$ = 0.1 ms; $V_{DS}$ ≤ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; starting at $T_j$ = 25 °C | | - | 280 | mJ |

[1] Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75 A.



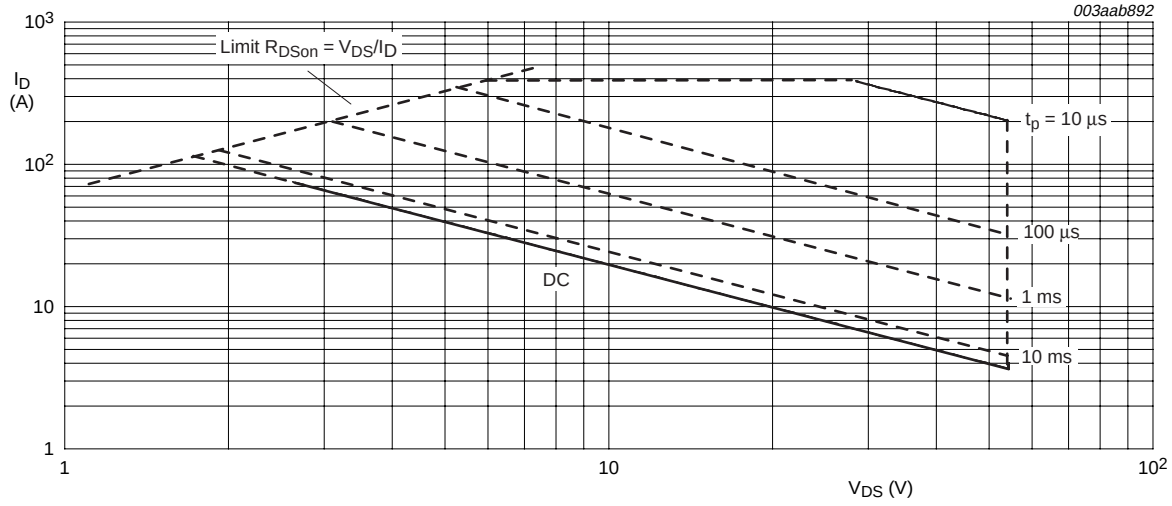

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

**Fig 1. Normalized total power dissipation as a function of mounting base temperature**




$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$

**Fig 2. Normalized continuous drain current as a function of mounting base temperature**




$T_{mb}$ = 25 °C; $I_{DM}$ is single pulse; $V_{GS}$ = 10 V

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 4. Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | - | 0.75 | K/W |
| $R_{th(j\text{-}a)}$ | thermal resistance from junction to ambient | vertical in free air | - | 60 | - | K/W |

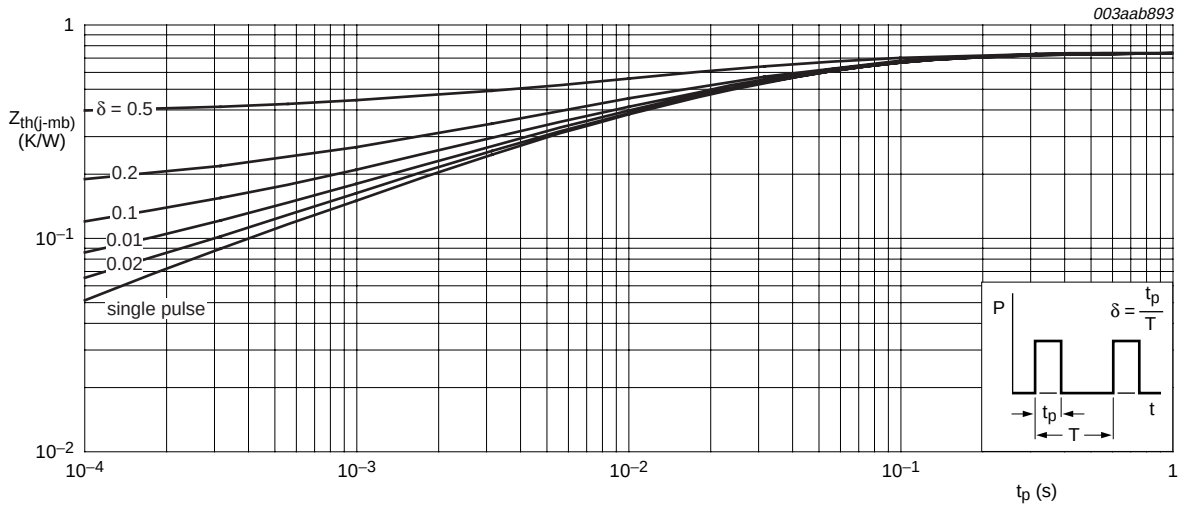


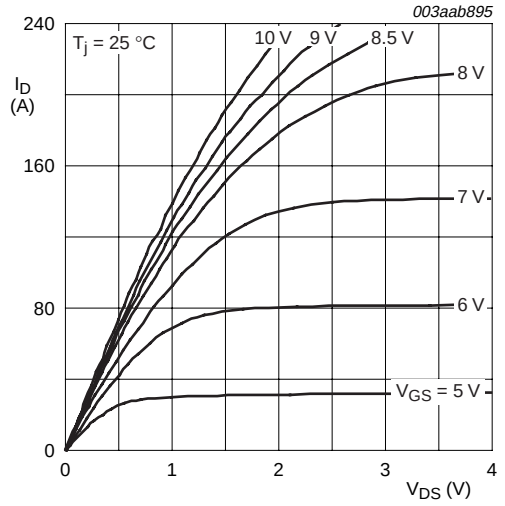

**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

**Table 5. Characteristics**

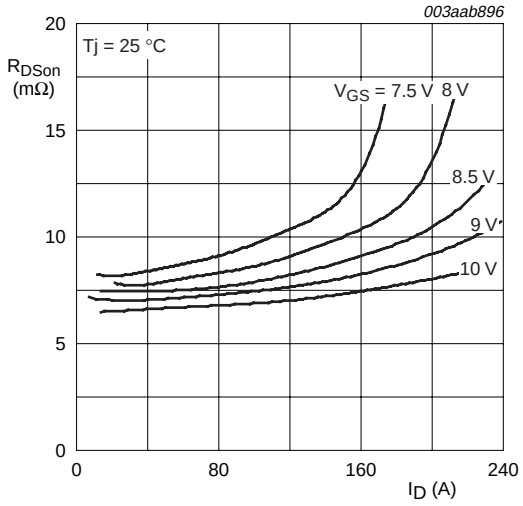
*$T_j$ = 25 °C unless otherwise specified.*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V | | | | |
| | | $T_j$ = 25 °C | 55 | - | - | V |
| | | $T_j$ = –55 °C | 50 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; see Figure 9 and 10 | | | | |
| | | $T_j$ = 25 °C | 2 | 3 | 4 | V |
| | | $T_j$ = 175 °C | 1 | - | - | V |
| | | $T_j$ = –55 °C | - | - | 4.4 | V |
| $I_{DSS}$ | drain leakage current | $V_{DS}$ = 55 V; $V_{GS}$ = 0 V | | | | |
| | | $T_j$ = 25 °C | - | - | 1 | µA |
| | | $T_j$ = 175 °C | - | - | 500 | µA |
| $I_{GSS}$ | gate leakage current | $V_{GS}$ = ±20 V; $V_{DS}$ = 0 V | - | 2 | 100 | nA |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 25 A; see Figure 6 and 8 | | | | |
| | | $T_j$ = 25 °C | - | 5.8 | 7.1 | mΩ |
| | | $T_j$ = 175 °C | - | 10.6 | 14.2 | mΩ |
| **Dynamic characteristics** | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D$ = 25 A; $V_{DS}$ = 44 V; $V_{GS}$ = 10 V; see Figure 11 and 12 | - | 53 | - | nC |
| $Q_{GS}$ | gate-source charge | | - | 12.3 | - | nC |
| $Q_{GD}$ | gate-drain charge | | - | 17 | - | nC |
| $C_{iss}$ | input capacitance | $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz; see Figure 14 | - | 2820 | - | pF |
| $C_{oss}$ | output capacitance | | - | 554 | - | pF |
| $C_{rss}$ | reverse transfer capacitance | | - | 200 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS}$ = 30 V; $R_L$ = 1.2 Ω; | - | 24 | - | ns |
| $t_r$ | rise time | $V_{GS}$ = 10 V; $R_G$ = 10 Ω | - | 52 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 77 | - | ns |
| $t_f$ | fall time | | - | 41 | - | ns |
| **Source-drain diode** | | | | | | |
| $V_{SD}$ | source-drain voltage | $I_S$ = 25 A; $V_{GS}$ = 0 V; see Figure 13 | - | 0.85 | 1.2 | V |
| $t_{rr}$ | reverse recovery time | $I_S$ = 20 A; $dI_S/dt$ = –100 A/µs; $V_{GS}$ = 0 V | - | 62 | - | ns |
| $Q_r$ | recovered charge | | - | 60 | - | nC |



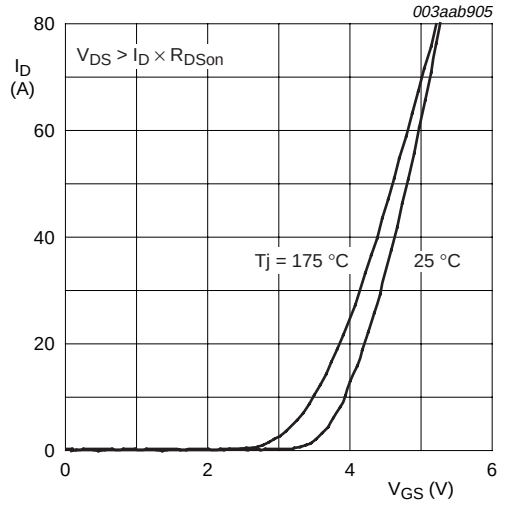

$T_j$ = 25 °C

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



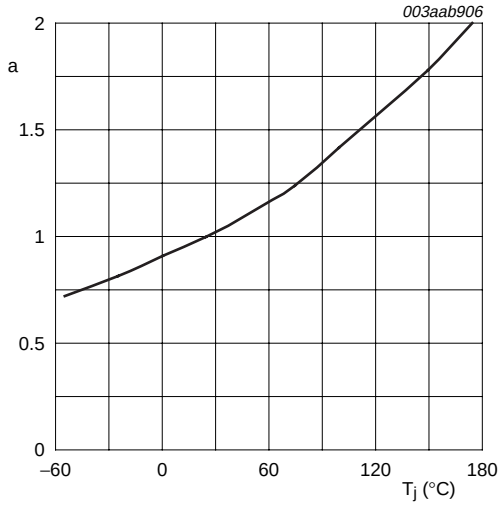

$T_j$ = 25 °C

**Fig 6. Drain-source on-state resistance as a function of drain current; typical values**



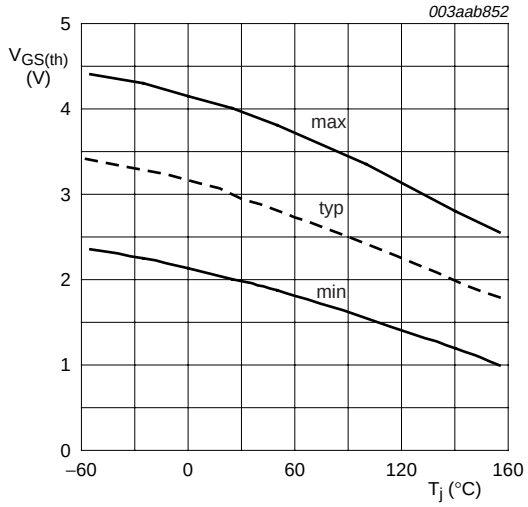

$T_j$ = 25 °C and 175 °C; $V_{DS} > I_D \times R_{DSon}$

**Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



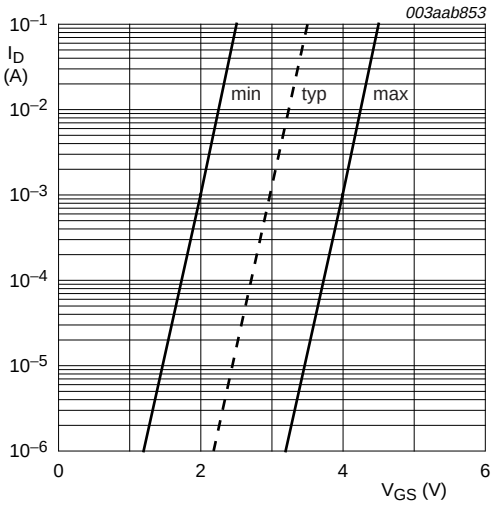

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature**



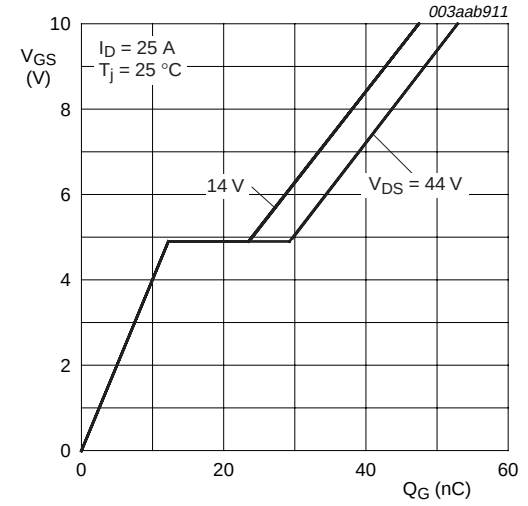

$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$

**Fig 9. Gate-source threshold voltage as a function of junction temperature**




$T_j$ = 25 °C; $V_{DS}$ = 5 V

**Fig 10. Sub-threshold drain current as a function of gate-source voltage**




$I_D$ = 25 A; $V_{DS}$ = 14 V and 44 V

**Fig 11. Gate-source voltage as a function of gate charge; typical values**

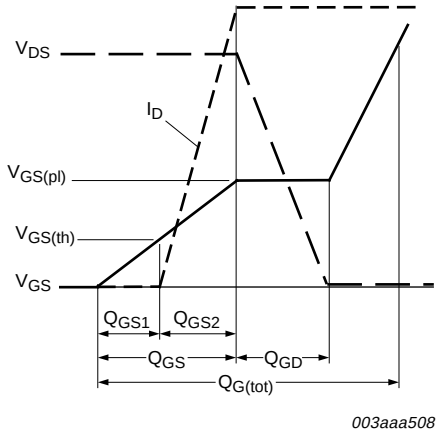
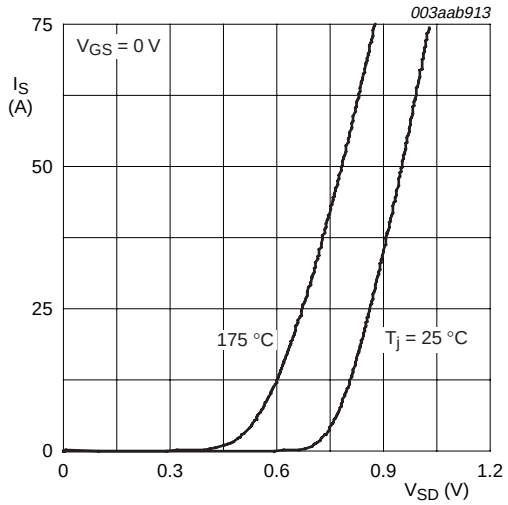
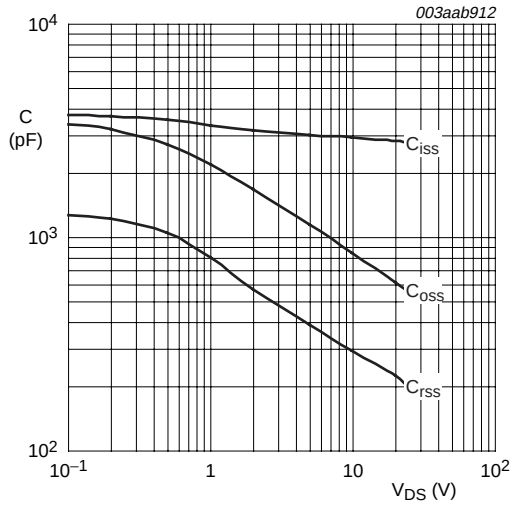



**Fig 12. Gate charge waveform definitions**




$T_j$ = 25 °C and 175 °C; $V_{GS}$ = 0 V

**Fig 13. Source current as a function of source-drain voltage; typical values**

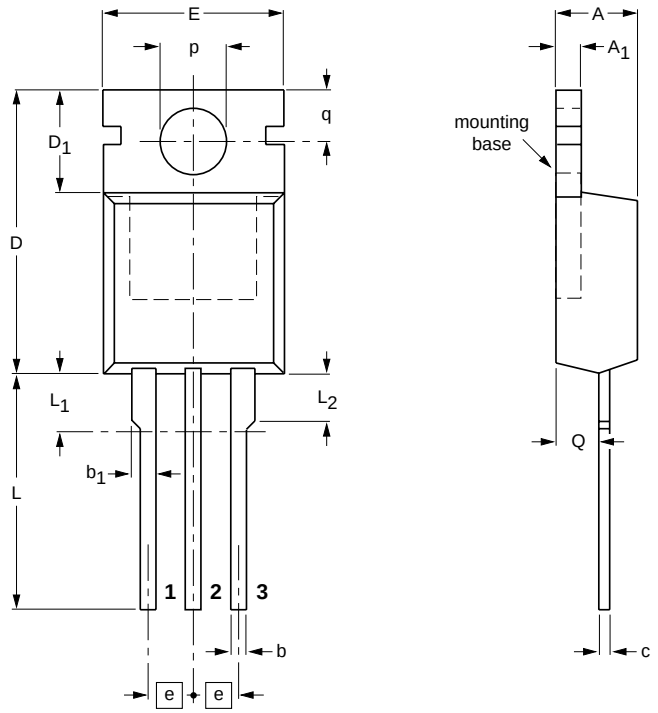



$V_{GS}$ = 0 V; f = 1 MHz

**Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

## 7. Package outline

**Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB** **SOT78**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A | $A_1$ | b | $b_1$ | c | D | $D_1$ | E | e | L | $L_1$ | $L_2$ max. | p | q | Q |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 4.7<br>4.1 | 1.40<br>1.25 | 0.9<br>0.6 | 1.45<br>1.00 | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9 | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79 | 3.0 | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT78 | | 3-lead TO-220AB | SC-46 | | | ~~05-03-22~~<br>05-10-25 |

**Fig 15. Package outline SOT78 (TO-220AB)**

## 8. Revision history

**Table 6. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| OC1005_2 | 20071210 | Product data sheet | - | OC1005_1 |
| Modifications: | • Figure 2 updated. | | | |
| OC1005_1 | 20070907 | Product data sheet | - | - |

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## 9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 11. Contents





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